210	210	210	210	210	210	210
Total N	umber of Page	es: 04			<u>B.TE</u> 15BE2	
	1	st Semester	Back Examina	tion 2016-17		
			S OF ELECTRO			
210	210	210	BRANCH: ALL Time: 3 Hours	210	210	210
		N	Max Marks: 100 Q.CODE: Y514			
			compulsory an	-		
	The hg				ai NS.	
<b>Q1</b> <sup>210</sup>		following ques	Answer all the qu tions: <i>multiple type</i>		<sup>210</sup> (2 x <sup>-</sup>	10)
a)	The period of (a) 1/40 s	• ,	5 + 40cos 80πt is			
	(b) 1/80 s	ec.				
	(c) 40π se (d) 80π se					
<sup>210</sup> <b>b)</b>			occurs because	210	210	210
	` '	ets reflected du Illing on the diod				
	` '	•	ae gets amplilied			
	(c) diode	gets heated up		nlace		
c)	(c) diode (d) recom If V <sub>m</sub> is the pe	gets heated up bination of char eak voltage acre	ge carriers takes poss the secondary	of a transformer		
,	(c) diode (d) recom If V <sub>m</sub> is the powave rectifie	gets heated up bination of char eak voltage acro r (without filter	ge carriers takes poss the secondary circuit), then the r	of a transformer maximum voltag	e on the	
<b>c)</b>	(c) diode (d) recom If V <sub>m</sub> is the per wave rectified reverse biase (a) V <sub>m</sub>	gets heated up bination of char eak voltage acro r (without filter	ge carriers takes poss the secondary	of a transformer		210
,	(c) diode (d) recom If V <sub>m</sub> is the perwave rectified reverse biase (a) V <sub>m</sub> (b) 2 V <sub>m</sub>	gets heated up bination of char eak voltage acro r (without filter ed diode is 210	ge carriers takes poss the secondary circuit), then the r	of a transformer maximum voltag	e on the	210
,	(c) diode (d) recom If V <sub>m</sub> is the per wave rectified reverse biase (a) V <sub>m</sub>	gets heated up bination of char eak voltage acro r (without filter ed diode is 210	ge carriers takes poss the secondary circuit), then the r	of a transformer maximum voltag	e on the	210
,	(c) diode (d) recom  If V <sub>m</sub> is the period wave rectified reverse biase (a) V <sub>m</sub> (b) 2 V <sub>m</sub> (c) 0.5 V <sub>m</sub> (d) 4 V <sub>m</sub> Compare to a	gets heated up bination of char eak voltage acro r (without filter ed diode is 210	ge carriers takes poss the secondary circuit), then the r	of a transformer naximum voltag	e on the	210
210	(c) diode (d) recom  If V <sub>m</sub> is the period wave rectified reverse biase (a) V <sub>m</sub> (b) 2 V <sub>m</sub> (c) 0.5 V <sub>m</sub> (d) 4 V <sub>m</sub> Compare to a (a) lower in	gets heated up bination of char eak voltage acro r (without filter ed diode is 210	ge carriers takes poss the secondary circuit), then the r	of a transformer naximum voltag	e on the	
210 <b>d)</b>	(c) diode (d) recom  If V <sub>m</sub> is the period (a) V <sub>m</sub> (b) 2 V <sub>m</sub> (c) 0.5 V <sub>m</sub> (d) 4 V <sub>m</sub> Compare to a (a) lower in (b) higher (c) lower in (d) diode (d) lower in (e) lower in (e) lower in (finite (d) lower in (finite (d) lower in (e) lo	gets heated up bination of char eak voltage acro (without filter ed diode is 210 a CB amplifier, to the coutput resistance output resistance current amplification of the coutput resistance current amplification of the coutput resistance the coutput resistance current amplification of the coutput resistance the coutput resistance current amplification of the coutput resistance the coutput	ge carriers takes poss the secondary circuit), then the results to the condition of the condition of the condition factor.	of a transformer maximum voltage 210	e on the	
210 <b>d)</b>	(c) diode (d) recom  If V <sub>m</sub> is the period wave rectified reverse biases  (a) V <sub>m</sub> (b) 2 V <sub>m</sub> (c) 0.5 V <sub>m</sub> (d) 4 V <sub>m</sub> Compare to a (a) lower in (b) higher (c) lower of (d) higher	gets heated up bination of chareak voltage across (without filter ed diode is 210 a CB amplifier, to the coutput resistance output resistance	ge carriers takes poss the secondary circuit), then the results to the condition of the condition of the condition factor.	of a transformer maximum voltage 210	e on the	210
210 d)	(c) diode (d) recom (d) recom If V <sub>m</sub> is the per wave rectified reverse biase (a) V <sub>m</sub> (b) 2 V <sub>m</sub> (c) 0.5 V <sub>m</sub> (d) 4 V <sub>m</sub> Compare to a (a) lower in (b) higher (c) lower (d) higher An ideal Op-a (a) voltage	gets heated up bination of char eak voltage acro (without filter ed diode is 210 a CB amplifier, to the coutput resistance output resistance current amplificamp is an ideal e controlled cur	ge carriers takes poss the secondary circuit), then the result of the certain factor cation factor rent source	of a transformer maximum voltage 210	e on the	
210 d)	(c) diode (d) recom  If V <sub>m</sub> is the period wave rectified reverse biases (a) V <sub>m</sub> (b) 2 V <sub>m</sub> (c) 0.5 V <sub>m</sub> (d) 4 V <sub>m</sub> Compare to a (a) lower in (b) higher (c) lower of (d) higher An ideal Op-a (a) voltage (b) voltage (b) voltage	gets heated up bination of char eak voltage acro (without filter ed diode is 210 a CB amplifier, to the current amplificamp is an ideal	ge carriers takes poss the secondary circuit), then the results to the certain factor cation factor rent source rage source	of a transformer maximum voltage 210	e on the	

The propagation delay of each inverter is 100µs. find the fundamental

frequency of the oscillator output Vo.

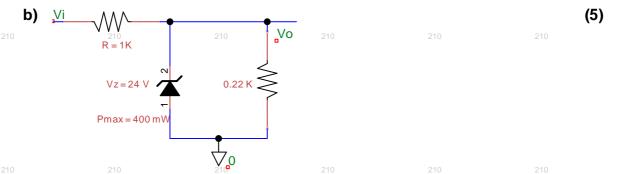
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Determine Vo for the above circuit.

j) Mention the conditions that must be fulfilled for sustained oscillation.

Q3 a) Draw the circuit diagram of a full wave bridge type rectifier using diode and explain its operation. Derive the expressions for rectification efficiency and ripple factor, form factor and the transformer utilization factor.



Determine the range of Vi that will maintain Vo at 24 volt without exceeding the power rating of the zener diode.

Q4 a) What is the need of biasing in a transistor amplifier? Draw and explain the circuit of a voltage divider bias CE amplifier. Derive the expression for the stability factor due to I<sub>CO</sub> for this configuration.

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2.

Determine the Q point for the configuration shown in the figure. Assume the  $\beta$  of the transistor as 75 and capacitors are 10  $\mu$ f.

- Q5 a) Implement a full adder circuit using two 4:1 multiplexors. (10)
  - 210 **b)** State and prove DeMorgan's theorem of Boolean algrbra. (5)
- Q6 a) Draw and explain the circuit of a Wien bridge oscillator. Derive an expression for the frequency of oscillation for this oscillator.
  - b) The distortion in an amplifier is found to be 2% when the feedback factor of a negative a feedback amplifier is 0.04. When the feedback is removed, the distortion becomes 10%. Find the open loop gain and closed loop gain of the amplifier.
- Q7 a) Draw the circuit of a basic differentiator and explain its operation. What are the limitations of this circuit and how these are overcome in practical differentiator circuit?
  - b) IC 741 is used as an inverting amplifier with a gain of 100. The frequency response plot is flat up to 10 KHz. Determine the maximum peak to peak signal that can be applied without distortion to the output.
- **Q8 a)** With the help of block diagram showing essential components explain the working of CRO. (10)
  - b) What is Lissajous method? Does it require sweep signal? How is Lissajous pattern useful in frequency and phase measurement of a signal
- Q9 a) Draw the circuit of an emitter follower. Derive the expression for input impedance, output impedance and the voltage gain. (10)
  - b) Differentiate between static and dynamic RAM. (5)